

4. (Original): A microelectronic structure according to claim 1, wherein said metal layer comprises Cu or Cu alloy.
5. (Original): A microelectronic structure according to claim 1, wherein said metal layer comprises Al or Al alloy.
6. (Original): A microelectronic structure according to claim 1, wherein said layer of high dielectric constant material comprises a complex metal oxide selected from the group consisting of $\text{SrBi}_2\text{Ta}_2\text{O}_9$ (SBT), $(\text{Ba,Sr})\text{TiO}_3$ (BST), BiTaO_4 (BT), and $\text{Pb}(\text{Zr,Ti})\text{O}_3$ (PZT).
7. (Original): A microelectronic structure according to claim 1, wherein said layer of high dielectric constant material comprises perovskite BST material.
8. (Original): A microelectronic structure according to claim 1, wherein said layer of high dielectric constant material comprises amorphous BST material.
9. (Original): A microelectronic structure according to claim 1, wherein said conductive barrier layer has a thickness in a range of from about 1nm to about 100nm.
10. (Original): A microelectronic structure according to claim 1, wherein said conductive barrier layer has a thickness in a range of from about 5nm to about 20nm.
11. (Original): A microelectronic structure according to claim 1, wherein said conductive barrier layer comprises Pt.
12. (Original): A microelectronic structure according to claim 1, wherein said conductive barrier layer comprises Ir.